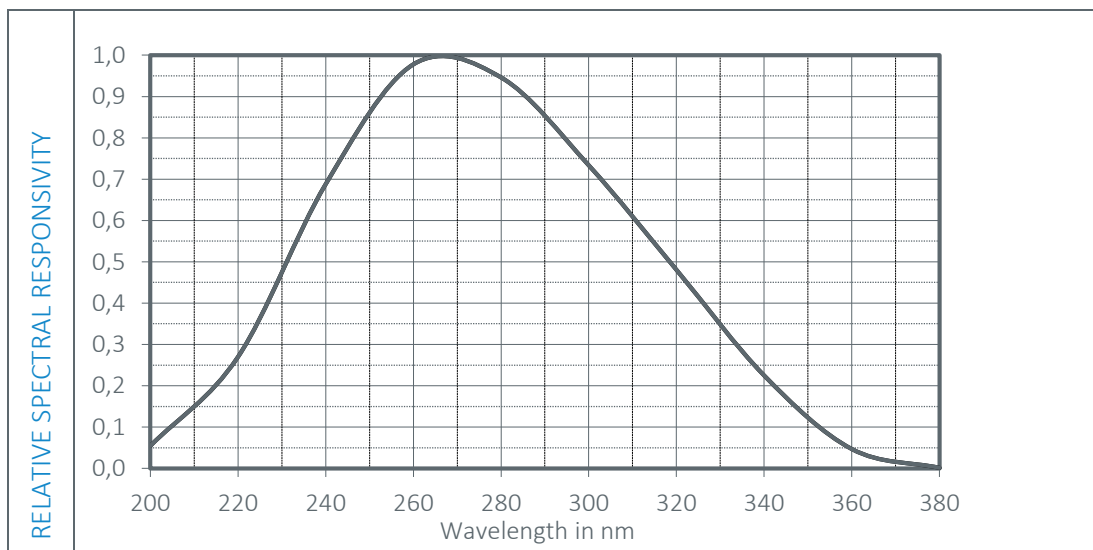


SiC-Photodiodes for UV-Detection

OVERVIEW	Visible blind UV sensors with SiC semiconductor
	Proven long-term stability under high UV-C-radiation (up to 1000 Wm ⁻²)
	Excellent temperature stability (temperature coefficient T _k < 0,06%/K)
	Option for integrated transimpedance amplifiers
	Low dark current (fA-range)
	Hermetically sealed TO packages
	RoHS, REACH, WEEE conform

APPLICATIONS	General UV-range photo detection
	Selective UV measurements (UV-A, UV-B, UV-C, etc...)
	Flame control
	Sterilization lamp control
	Laser monitoring
	Medical applications (erythema sensors)



ACTIVE AREAS	0,05 mm ²	square
	0,1 mm ²	square
	0,25 mm ²	square
	1 mm ²	square
	2 mm ²	square
	5 mm ²	circular
	4 x 1,25 mm ²	circular





VARIANTS	PACKAGES	POLARITY	TEMPERATURE	OPTIONS
	TO5	anode isolated	regular: 125 °C	lens caps
	TO18	cathode isolated	high temperature 150°C	diffusors
	TO52	fully isolated assembly		apertures

FILTER OPTIONS	POPULAR FILTERS:	
	UV-A	320–380 nm
	UV-B	280–320 nm
	UV-C	210–280 nm
	FURTHER STANDARD FILTERS:	
	UV-BC	210–320 nm
	UV-AB	280–380 nm
	Erythema	CIE 87
	DVGW	240–290 nm
	UV-A-350	300–400 nm
	UV-A-365	350-400 nm

AMPLIFIER OPTIONS	Operating voltage	+ 2,7...+ 13,2 V + 2,7...+ 5,5 V bipolar supplies on request
	Transimpedance-values	10 MOhm 100 MOhm 1000 MOhm custom versions on request
	Options	low supply current version high bandwidth versions

